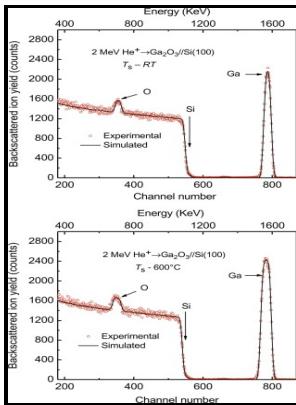


Gallium diffusion in silicon dioxide - Rutherford backscattering analysis of thin film.

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Description: -

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Notes: MSc thesis, Electrical Engineering.

This edition was published in 1975



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Tags: #Atomic #layer #deposition #of #tin #dioxide #sensing #film #in #microhotplate #gas #sensors

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Due to the self-saturating nature of the process, ALD enables almost perfectly conformal deposition of films on an atomic level and precise control of the thickness and composition of the deposited films. After the reaction the reaction space is purged carefully with an inert gas to remove the unreacted source material and the reaction products from the reaction space.

Structural and Optical Characteristics of Gallium Oxide Thin Films Deposited by Ultrasonic Spray Pyrolysis

V Method of cyclic dry etching using etchant film 2016-07-19 2020-07-14 Asm Ip Holding B. As discussed below, other oxygen sources, such as atomic oxygen, oxygen plasma or oxygen radicals, can be used.

US8501637B2

Since the depth of the trench is greater than the width STI requires a method which is capable of filling the etched isolation trench conformally. Method for forming dielectric film in trenches by PEALD using H-containing gas 2015-12-01 2018-02-27 Asm Ip Holding B. The function of STI is to isolate the transistors from each other in both the circuit and memory structures.

Structural and Optical Characteristics of Gallium Oxide Thin Films Deposited by Ultrasonic Spray Pyrolysis

Semiconductor reaction chamber showerhead 2012-12-26 2017-05-02 Asm Ip Holding B. It is important to note that for annealed samples, and even for the as-deposited films, there is no signal related with the existence of O-H radicals. Non-single crystal semiconductor material formed on a semiconductor substrate and separated from all but a portion of the substrate by an intervening insulation layer contains at least one dopant and preferably two dopants of opposite conductivity type.

Structural and Optical Characteristics of Gallium Oxide Thin Films Deposited by Ultrasonic Spray Pyrolysis

Methods for thermally calibrating reaction chambers 2016-11-01 2019-10-08 Asm Ip Holding B. Methods of depositing metal films using metal oxyhalide precursors 2018-10-26 2020-07-14 Globalfoundries Inc.

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In some embodiments the removal of excess reactant comprises continuing to flow purge gas for between about 0. This change in the refractive index value, in comparison with that of the as-deposited films, is explained by the crystalline nature of the annealed films which have a more compact microstructure.

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Preferably, each ALD cycle comprises at least two distinct phases. Dual section module having shared and unshared mass flow controllers 2011-07-15 2020-12-01 Asm Ip Holding B.

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